NSN 5962-01-168-3366

Memory Microcircuit - Page 1 of 2



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Body Length: 1.290 inches Body Width: Between 0.500 inches and 0.610 inches Body Height: Between 0.150 inches and 0.210 inches Maximun Power Dissipation Rating: 950.0 milliwatts Operating Tempurature Range: -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius Peatures Provided: Hermetically sealed and programmable and wienable and 3-state output Inclosure Material: Ceramic and glass Inclosure Material: Ceramic and glass Inclosure Material: Output Logic Form: Transistor-Iransistor logic Input Grani: 14 input Case Outline Source And Designator: 19.3 mil-m38510 Positing Surface Treatment: Solder Voltage Rating And Type Per Characteristic: 15. volts power source Time Rating Per Chateristic: 12.0.0 nanoseconds propagation delay time, low to high level output Memory Device Type: Rom 12.000 nanoseconds propagation delay time, low to high level output	
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96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity: 24 printed circuit	Rom
Terminal Type And Quantity: 24 printed circuit	Test Data Document:
24 printed circuit	96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
	Terminal Type And Quantity:
Shelf Life:	24 printed circuit
	Shelf Life:
N/a	N/a
Unit Of Measure:	Unit Of Measure:
	Demilitarization:
	Yes - demil/mli
 Demilitarization:	

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